

60V PNP MEDIUM POWER TRANSISTOR IN SOT89

Description

Packaged in SOT89 outline, this low-saturation PNP transistor offers extremely low on-state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

Mechanical Data

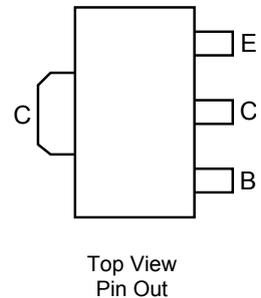
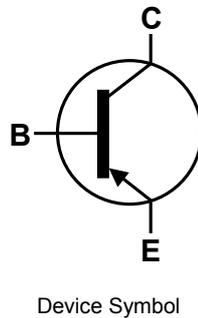
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads,
Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.05 grams (Approximate)

Features

- $BV_{CEO} > -60V$
- $BV_{ECO} > -7V$
- $I_C = -4.5$ High Continuous Collector Current
- $I_{CM} = -7A$ Peak Collector Current
- $V_{CE(sat)} < -80mV @ -1A$
- $R_{CE(sat)} = 50m\Omega$ for a Low Equivalent On-Resistance
- $P_D = 2.4W$
- Complementary Part Number ZXTN19060CZ
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Applications

- High Side Driver
- Motor Drive
- Load Disconnect Switch

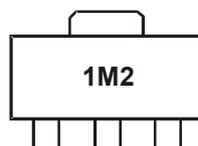


Ordering Information (Notes 4)

| Product | Marking | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|---------------|---------|--------------------|-----------------|-------------------|
| ZXTP19060CZTA | 1M2 | 7 | 12 | 1000 |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



1M2 = Product Type Marking Code

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Limit | Unit |
|--|-----------|-------|------|
| Collector-Base Voltage | V_{CBO} | -60 | V |
| Collector-Emitter Voltage | V_{CEO} | -60 | V |
| Emitter-Collector Voltage (Reverse Blocking) | V_{ECX} | -7 | V |
| Emitter-Base Voltage | V_{EBO} | -7 | V |
| Continuous Collector Current | I_C | -4.5 | A |
| Peak Pulse Current | I_{CM} | -7 | A |
| Base Current | I_B | -1 | A |

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

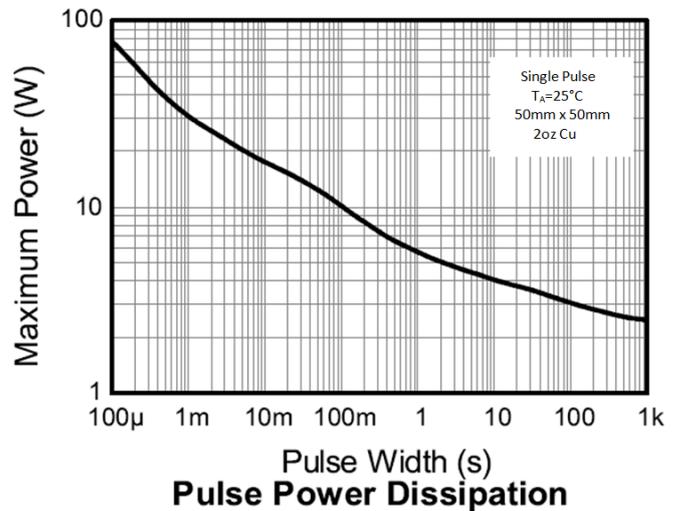
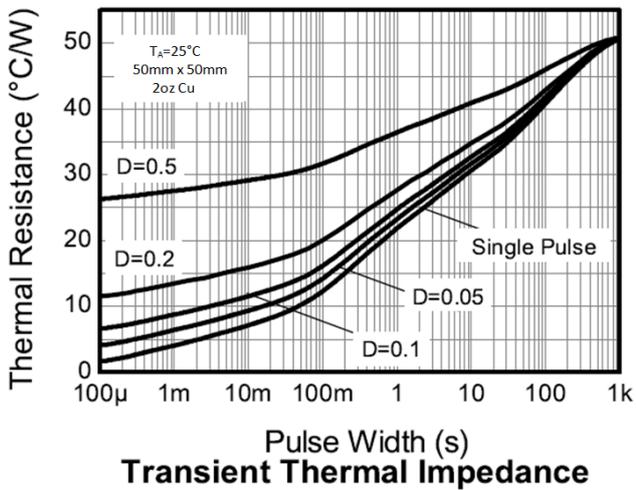
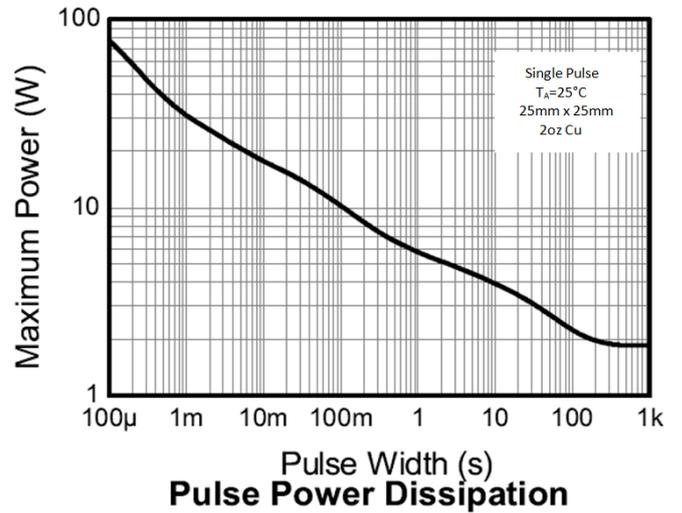
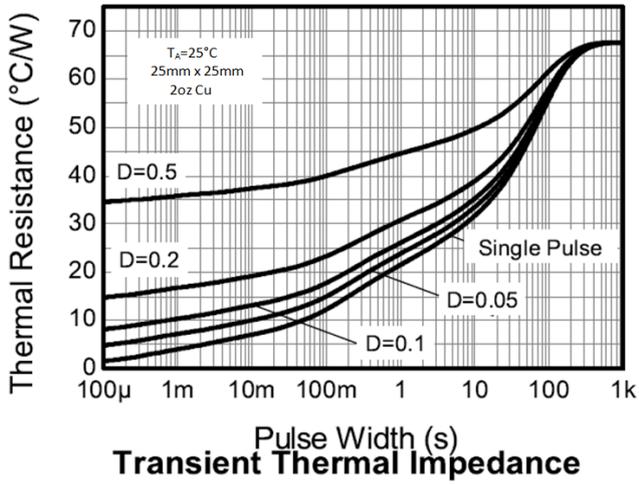
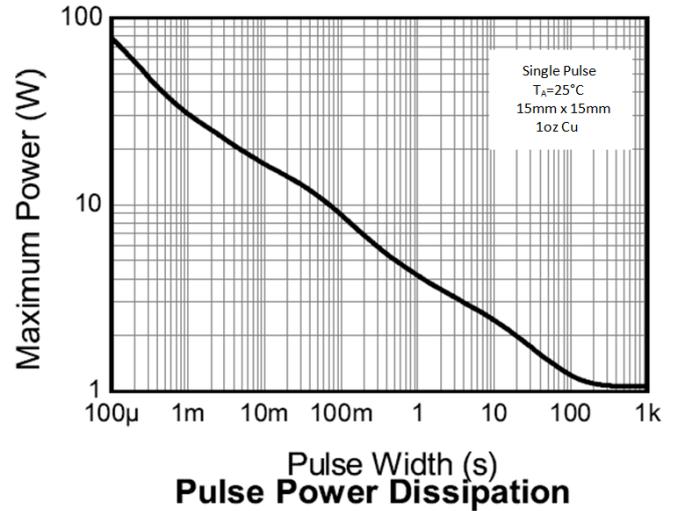
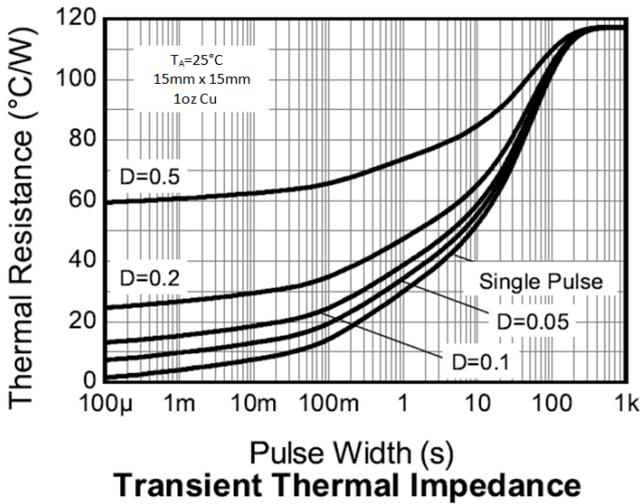
| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------------|---------------------------|
| Power Dissipation Linear Derating Factor | (Note 5) | 1.1 | W mW/ $^\circ\text{C}$ |
| | (Note 6) | 8.8 | |
| | (Note 7) | 1.8 | |
| | (Note 8) | 14.4 | |
| | (Note 9) | 2.4 | |
| | (Note 9) | 19.2 | |
| Thermal Resistance, Junction to Ambient Air | $R_{\theta JA}$ | 4.46 | $^\circ\text{C/W}$ |
| | | 35.7 | |
| | | 26.7 | |
| | | 213 | |
| Thermal Resistance, Junction to Lead | $R_{\theta JL}$ | 117 | $^\circ\text{C/W}$ |
| | | 68 | |
| | | 51 | |
| | | 31 | |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

ESD Ratings (Note 10)

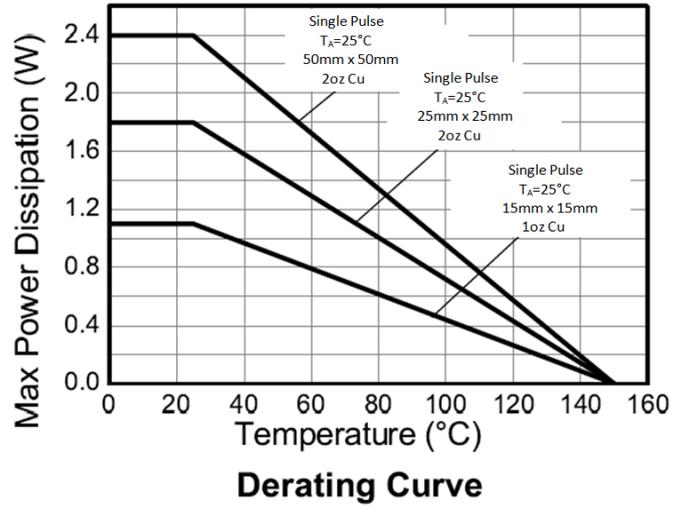
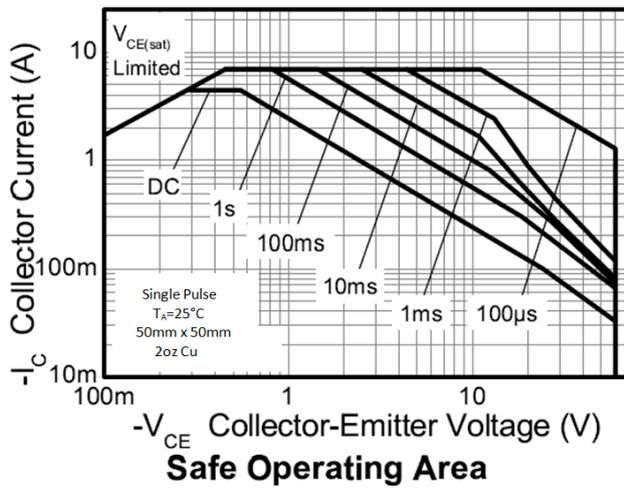
| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | C |

- Notes:
5. For a device mounted with the exposed collector pad on 15mm × 15mm 1oz copper that is on a single-sided 0.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
 7. Same as Note 5, except the device is mounted on 50mm × 50mm 2oz copper.
 8. Same as Note 7, except the device is measured at $t < 10$ seconds.
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



Thermal Characteristics and Derating Information (cont.)

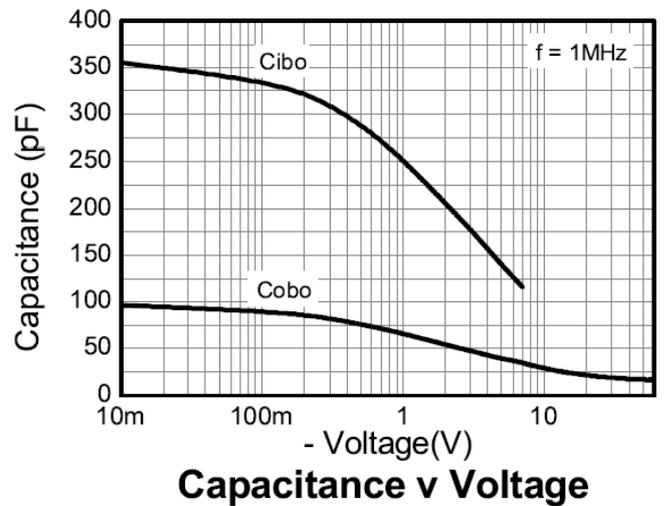
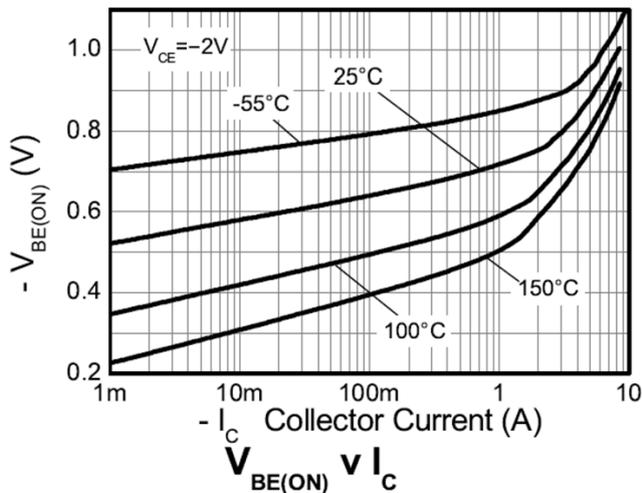
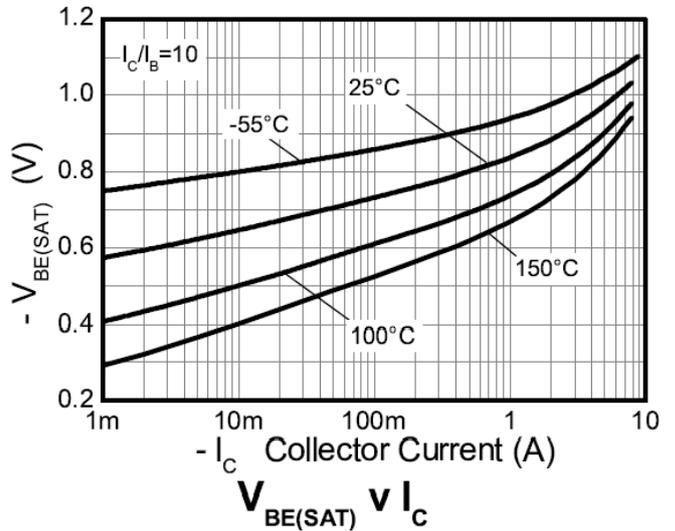
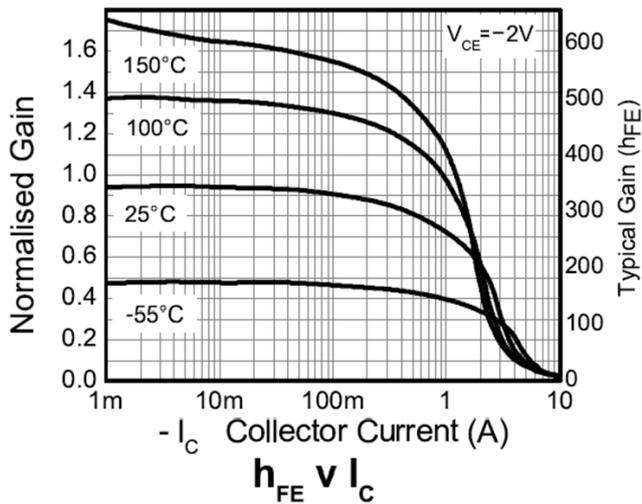
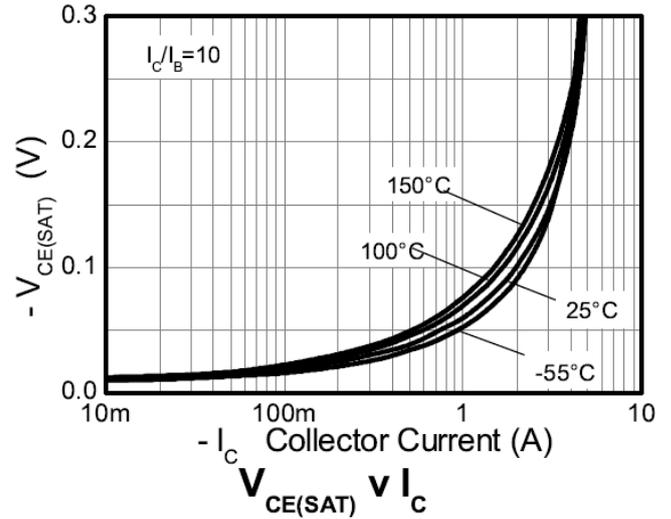
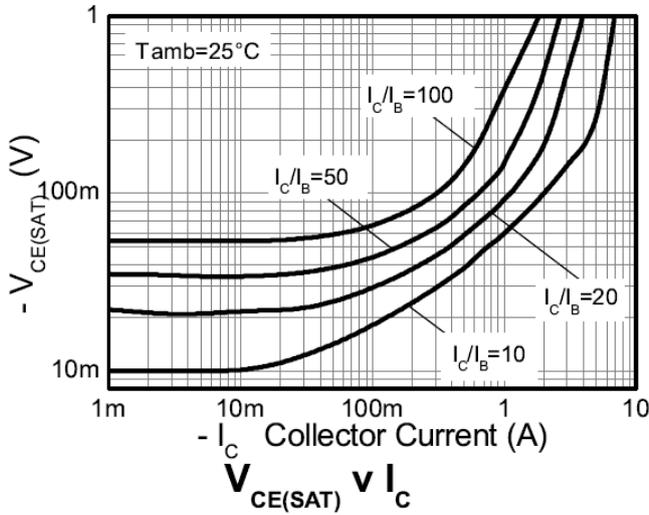


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------|------------------|---|---|------|--|
| Collector-Base Breakdown Voltage | BV_{CBO} | -60 | -110 | — | V | $I_C = -100\mu\text{A}$ |
| Collector-Emitter Breakdown Voltage (Note 11) | BV_{CEO} | -60 | -90 | — | V | $I_C = -10\text{mA}$ |
| Emitter-Collector Breakdown Voltage (Reverse Blocking) | BV_{ECX} | -7 | -8.4 | — | V | $I_E = -100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$ |
| Emitter-Collector Breakdown Voltage (Reverse Blocking) | BV_{ECO} | -7 | -8.8 | — | V | $I_E = -100\mu\text{A}$ |
| Emitter-Base Breakdown Voltage | BV_{EBO} | -7 | -8.4 | — | V | $I_E = -100\mu\text{A}$ |
| Collector-Base Cutoff Current | I_{CBO} | — | -1 | -50 | nA | $V_{CB} = -60\text{V}$ |
| Emitter Cutoff Current | I_{EBO} | — | -1 | -50 | nA | $V_{CB} = -60\text{V}$, $T_A = +100^\circ\text{C}$ |
| DC Current Transfer Static Ratio (Note 11) | h_{FE} | 200 160 25 | 330 260 45 | 500 | — | $I_C = -100\text{mA}$, $V_{CE} = -2\text{V}$ $I_C = -1\text{A}$, $V_{CE} = -2\text{V}$ $I_C = -4.5\text{A}$, $V_{CE} = -2\text{V}$ |
| Collector-Emitter Saturation Voltage (Note 11) | $V_{CE(sat)}$ | — | -62 -150 -500 -105 -145 -240 | -80 -205 -750 -165 -200 -410 | mV | $I_C = -1\text{A}$, $I_B = -100\text{mA}$ $I_C = -1\text{A}$, $I_B = -20\text{mA}$ $I_C = -2\text{A}$, $I_B = -40\text{mA}$ $I_C = -2\text{A}$, $I_B = -200\text{mA}$ $I_C = -3\text{A}$, $I_B = -300\text{mA}$ $I_C = -4.5\text{A}$, $I_B = -450\text{mA}$ |
| Base-Emitter Saturation Voltage (Note 11) | $V_{BE(sat)}$ | — | -965 | -1050 | mV | $I_C = -4.5\text{A}$, $I_B = -450\text{mA}$ |
| Base-Emitter Turn-on Voltage (Note 11) | $V_{BE(on)}$ | — | -875 | -1000 | mV | $I_C = -4.5\text{A}$, $V_{CE} = -2\text{V}$ |
| Transitional Frequency | f_T | — | 180 | — | MHz | $I_E = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$ |
| Input Capacitance | C_{ibo} | — | 280 | 400 | pF | $V_{EB} = -0.5\text{V}$, $f = 1\text{MHz}$, |
| Output Capacitance | C_{obo} | — | 29.5 | 40 | pF | $V_{CB} = -10\text{V}$, $f = 1\text{MHz}$, |
| Delay Time | t_d | — | 24.3 | — | ns | $I_C = -500\text{mA}$, $V_{CC} = -10\text{V}$, $I_{B1} = -I_{B2} = -50\text{mA}$ |
| Rise Time | t_r | — | 13.2 | — | ns | |
| Storage Time | t_s | — | 456 | — | ns | |
| Fall Time | t_f | — | 68.2 | — | ns | |

Note: 11. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

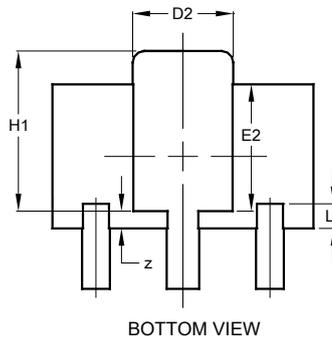
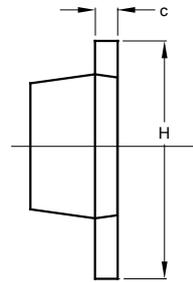
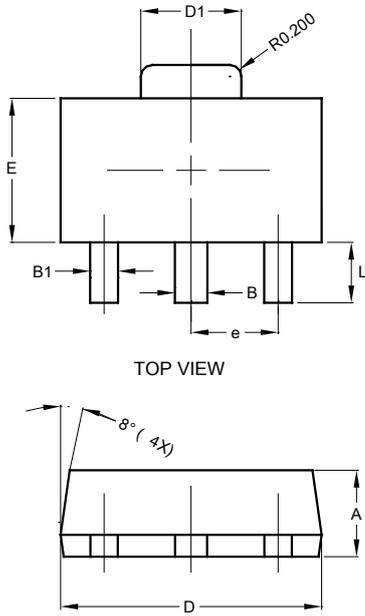
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89

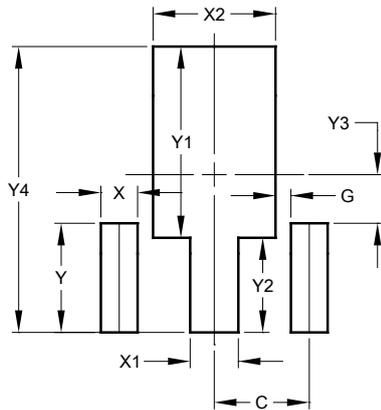


| SOT89 | | | |
|----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 1.40 | 1.60 | 1.50 |
| B | 0.50 | 0.62 | 0.56 |
| B1 | 0.42 | 0.54 | 0.48 |
| c | 0.35 | 0.43 | 0.38 |
| D | 4.40 | 4.60 | 4.50 |
| D1 | 1.62 | 1.83 | 1.733 |
| D2 | 1.61 | 1.81 | 1.71 |
| E | 2.40 | 2.60 | 2.50 |
| E2 | 2.05 | 2.35 | 2.20 |
| e | - | - | 1.50 |
| H | 3.95 | 4.25 | 4.10 |
| H1 | 2.63 | 2.93 | 2.78 |
| L | 0.90 | 1.20 | 1.05 |
| L1 | 0.327 | 0.527 | 0.427 |
| z | 0.20 | 0.40 | 0.30 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.500 |
| G | 0.244 |
| X | 0.580 |
| X1 | 0.760 |
| X2 | 1.933 |
| Y | 1.730 |
| Y1 | 3.030 |
| Y2 | 1.500 |
| Y3 | 0.770 |
| Y4 | 4.530 |

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